



VERY LOW RON SWITCHING
SILICON EPITAXIAL JUNCTION
N-CHANNEL FIELD EFFECT TRANSISTOR

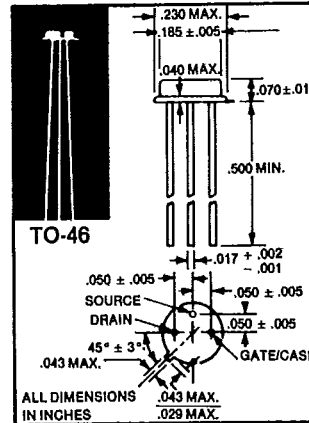
CM800

GEOMETRY 446

- LOW R_{DS} – 30 Ohms MAXIMUM
- LOW V_p – 7 Volts MAXIMUM
- HIGH I_{DSS} – 30 mA MINIMUM

ELECTRICAL DATA ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	CM800	UNITS
Drain to Gate Voltage	BV_{DGO}	30	Volts
Gate to Source Voltage	BV_{GSO}	-30	Volts
Peak Forward Gate Current	I_{GF}	100	mA
Peak Drain Current	I_D	400	mA
Power Dissipation (free air)	P_D	400	mW
Derating Factor (free air)	D_F	2.3	mW/°C
Junction Temp. (Oper. & Store)	T_J	-65°C to +200°C	
Lead Temp. (@ 1/16" to 1/32" from case)	T_L	240°C for 10 sec.	



ELECTRICAL CHARACTERISTICS: $T_A = 25^\circ C$ (UNLESS OTHERWISE STATED)

PARAMETERS and CONDITIONS	SYMBOL	CONDITION	CM800			UNITS
			Min.	Typ.	Max.	
Gate Leakage Current	I_{GSS}	$V_{GS} = -15V, V_{DS} = 0$	-	-	0.4	nA
Gate Leakage Current	I_{GSS}	$V_{GS} = -15V, V_{DS} = 0, T_A = 125^\circ C$	-	-	1.0	μA
Drain Cutoff Current	$I_{D OFF}$	$V_{GS} = -7V, V_{DS} = 5V$	-	-	0.4	nA
Drain Cutoff Current	$I_{D OFF}$	$V_{GS} = -7V, V_{DS} = 5V, T_A = 125^\circ C$	-	-	1.0	μA
Pinch-Off Voltage	V_{PO}	$V_{DS} = 5V, I_{DS} = 1nA$	1.0	4.0	7.0	Volts
On Resistance	R_{DS}	$V_{GS} = 0, I_{DS} = 1mA$	10	20	30	Ohms
Drain Current*	I_{DSS}	$V_{DS} = 10V, V_{GS} = 0$	30	-	-	mA
Gate to Source Cap.	C_{GS}	$V_{GS} = -20V$	-	5	6	pfd
Gate to Drain Cap.	C_{GD}	$V_{GD} = -20V$	-	5	6	pfd

* Pulse Measurement 1% Duty Cycle 10mS Max.



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